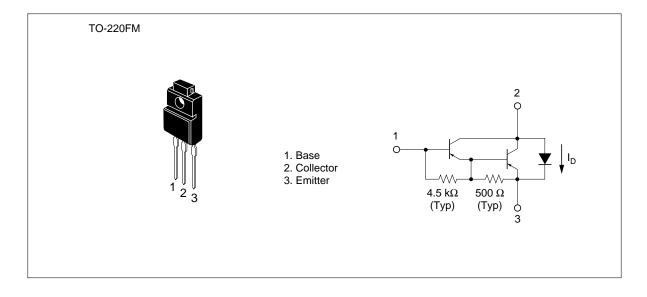
Silicon PNP Triple Diffused

HITACHI

Application

Low frequency power amplifier

Outline





Absolute Maximum Ratings ($Ta = 25^{\circ}C$)

Item	Symbol	Ratings	Unit	
Collector to base voltage	V_{CBO}	-60	V	
Collector to emitter voltage	V _{CEO}	-60	V	
Emitter to base voltage	V_{EBO}	-7	V	
Collector current	I _c	-4	A	
Collector peak current	I _{C(peak)}	-8	A	
Collector power dissipation	P _c	2	W	
	P _C *1	25		
Junction temperature	Tj	150	°C	
Storage temperature	Tstg	-55 to +150	°C	
C to E diode forward current	I _D *1	4	A	

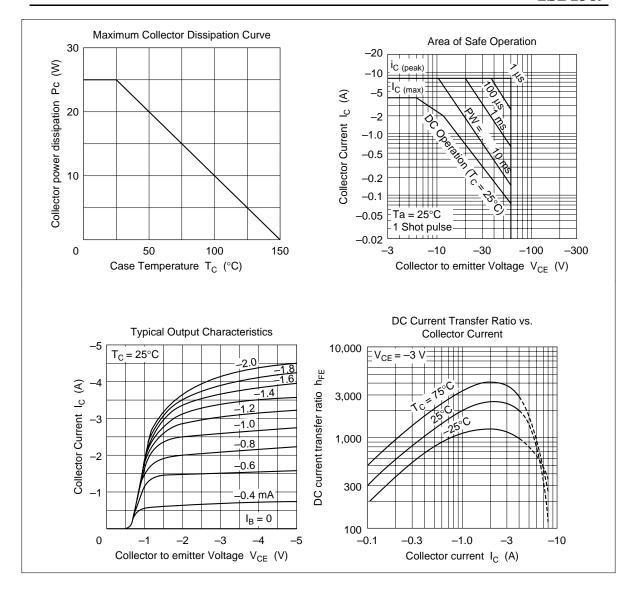
Note: 1. Value at $T_c = 25$ °C.

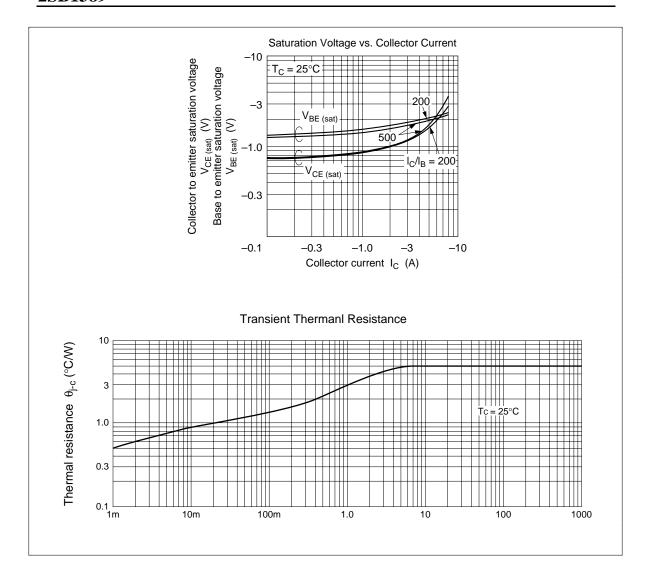
Electrical Characteristics ($Ta = 25^{\circ}C$)

Item	Symbol	Min	Тур	Max	Unit	Test conditions
Collector to base breakdown voltage	$V_{(BR)CBO}$	-60	_	_	V	$I_{c} = -0.1 \text{ mA}, I_{E} = 0$
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	-60		_	V	$I_{\rm C}$ = -25 mA, $R_{\rm BE}$ =
Emitter to base breakdown voltage	$V_{(BR)EBO}$	- 7		_	V	$I_{\rm E} = -50 \text{ mA}, I_{\rm C} = 0$
Collector cutoff current	I _{CBO}	_	_	-10	μA	$V_{CB} = -50 \text{ V}, I_{E} = 0$
	I _{CEO}	_	_	-10	_	$V_{CE} = -50 \text{ V}, R_{BE} =$
DC current transfer ratio	h _{FE}	1000	_	20000		$V_{CE} = -3 \text{ V}, I_{C} = -2 \text{ A}^{*1}$
Collector to emitter saturation	V _{CE(sat)1}	_	_	-1.5	V	$I_{\rm C} = -2 \text{ A}, I_{\rm B} = -4 \text{ mA}^{*1}$
voltage	V _{CE(sat)2}	_	_	-3.0		$I_{\rm C} = -4 \text{ A}, I_{\rm B} = -40 \text{ mA}^{*1}$
Base to emitter saturation	$V_{\text{BE}(\text{sat})1}$	_	_	-2.0	V	$I_{\rm C} = -2 \text{ A}, I_{\rm B} = -4 \text{ mA}^{*1}$
voltage	V _{BE(sat)2}	_		-3.5	_	$I_{\rm C} = -4 \text{ A}, I_{\rm B} = -40 \text{ mA}^{*1}$
C to E diode forward voltage	V_D	_		3.0	V	$I_{D} = 4 A^{*1}$

Note: 1. Pulse test.

See switching characteristic curve of 2SB1101.





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